

1Mx8 bit Low Power and Low Voltage CMOS Static RAM

FEATURES

- Process Technology: TFT
- Organization: 1M x8
- Power Supply Voltage: 4.5–5.5V
- Low Data Retention Voltage: 2.0V(Min)
- Three state output and TTL Compatible
- Package Type: 44-TSOP2-400F/R

GENERAL DESCRIPTION

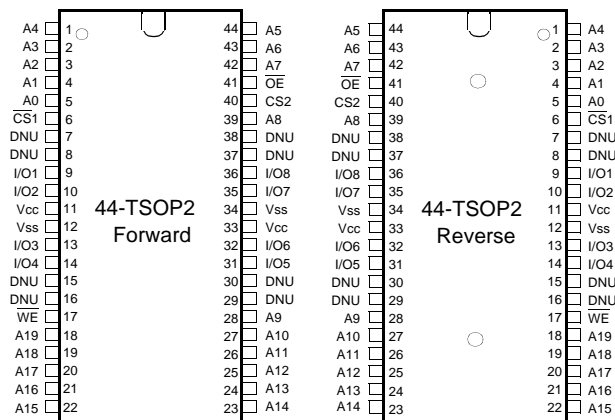
The K6T8008C2M families are fabricated by SAMSUNG's advanced CMOS process technology. The families support industrial operating temperature ranges for user flexibility of system design. The families also support low data retention voltage for battery back-up operation with low data retention current.

PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed	Power Dissipation		PKG Type
				Standby (I _{SB1} , Max)	Operating (I _{CC2} , Max)	
K6T8008C2M-B	Commercial(0~70°C)	4.5~5.5V	55 ¹⁾ /70ns	50μA	70mA	44-TSOP2-400F/R
K6T8008C2M-F	Industrial(-40~85°C)			80μA		

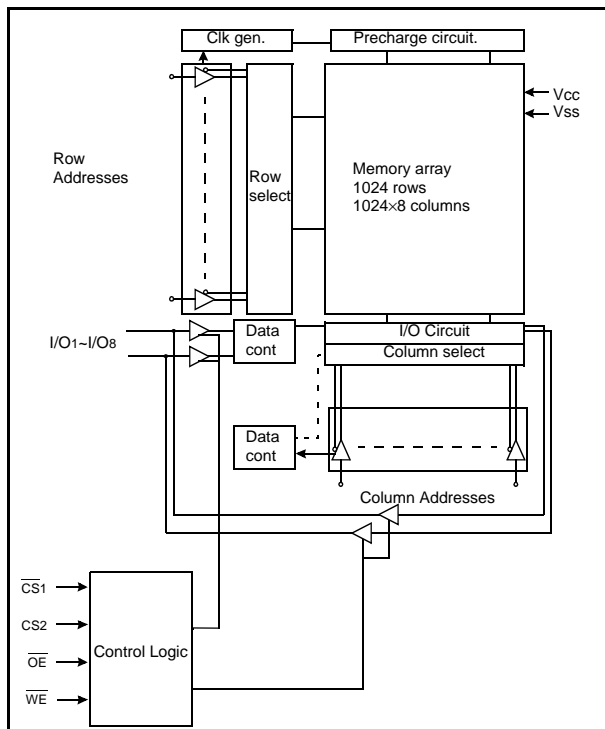
1. The parameter is measured with 50pF test load.

PIN DESCRIPTION



Name	Function	Name	Function
$\overline{CS1}$, $\overline{CS2}$	Chip Select Inputs	Vcc	Power
\overline{OE}	Output Enable Input	Vss	Ground
\overline{WE}	Write Enable Input	A0~A19	Address Inputs
I/O1~I/O8	Data Inputs/Outputs	DNU	Do Not Use

FUNCTIONAL BLOCK DIAGRAM



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